

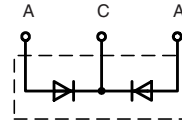
Power Schottky Rectifier with common cathode

$$I_{FAV} = 2 \times 15 \text{ A}$$

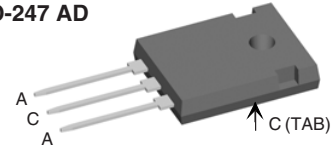
$$V_{RRM} = 45 \text{ V}$$

$$V_F = 0.42 \text{ V}$$

V_{RSM}	V_{RRM}	Type
V	V	
45	45	DSSK 30-0045B



TO-247 AD



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	Features
I_{FRMS}		50 A	<ul style="list-style-type: none"> • International standard package • Very low V_F • Extremely low switching losses • Low I_{RM}-values • Epoxy meets UL 94V-0
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$	15 A	
I_{FAV}	$T_C = 135^\circ\text{C}$; rectangular, $d = 0.5$; per device	30 A	
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	320 A	
E_{AS}	$I_{AS} = 15 \text{ A}$; $L = 180 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	32 mJ	Applications <ul style="list-style-type: none"> • Rectifiers in switch mode power supplies (SMPS) • Free wheeling diode in low voltage converters
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$; repetitive	1.5 A	
$(dv/dt)_{cr}$		1000 V/ μs	Advantages <ul style="list-style-type: none"> • High reliability circuit operation • Low voltage peaks for reduced protection circuits • Low noise switching • Low losses
T_{VJ}		-55...+150 $^\circ\text{C}$	
T_{VJM}		150 $^\circ\text{C}$	
T_{stg}		-55...+150 $^\circ\text{C}$	
P_{tot}	$T_C = 25^\circ\text{C}$	90 W	
M_d	mounting torque	0.8...1.2 Nm	
Weight	typical	6 g	

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$	10 mA	mA
	$V_R = V_{RRM}$; $T_{VJ} = 100^\circ\text{C}$	100 mA	mA
V_F	$I_F = 15 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.42 V	V
	$I_F = 15 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	0.47 V	V
	$I_F = 30 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.58 V	V
R_{thJC}		1.4 K/W	
R_{thCH}	0.25	K/W	

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0%
Data according to IEC 60747 and per diode unless otherwise specified:

Dimensions see Outlines.pdf

**Recommended replacement:
DSB30C45HB/DSB60C45HB**

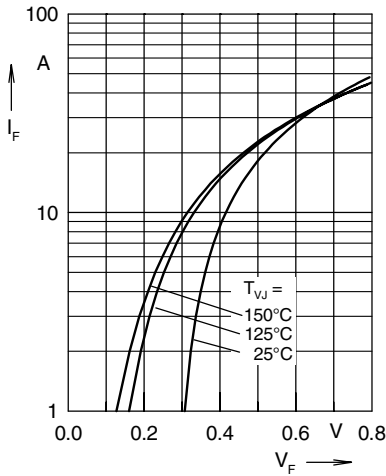


Fig. 1 Maximum forward voltage drop characteristics

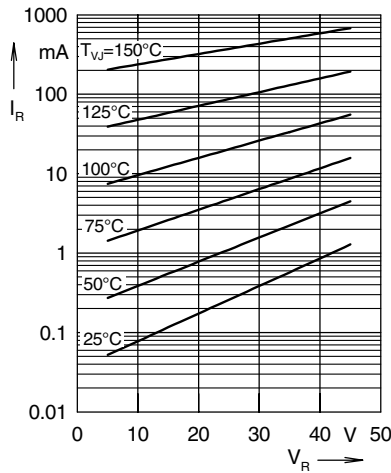


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

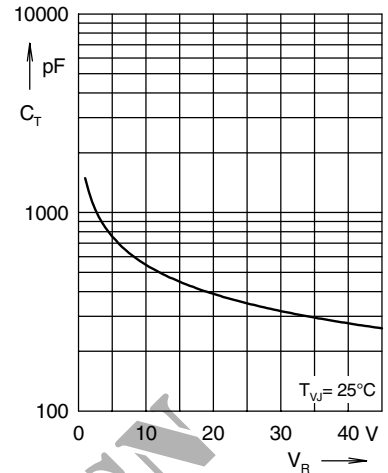


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

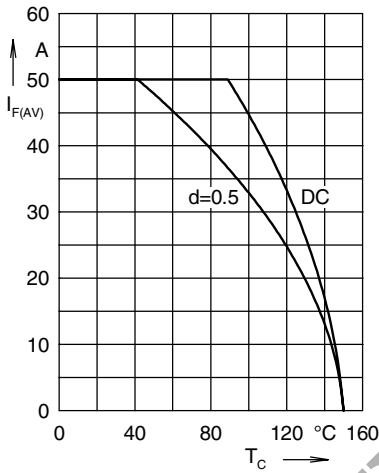


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

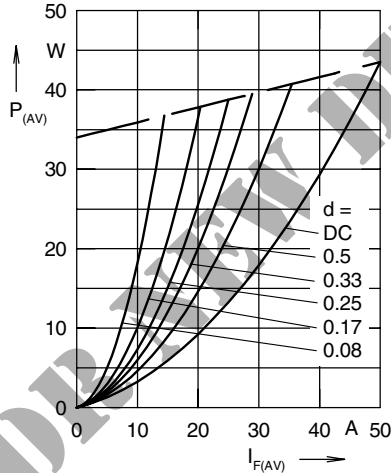


Fig. 5 Forward power loss characteristics

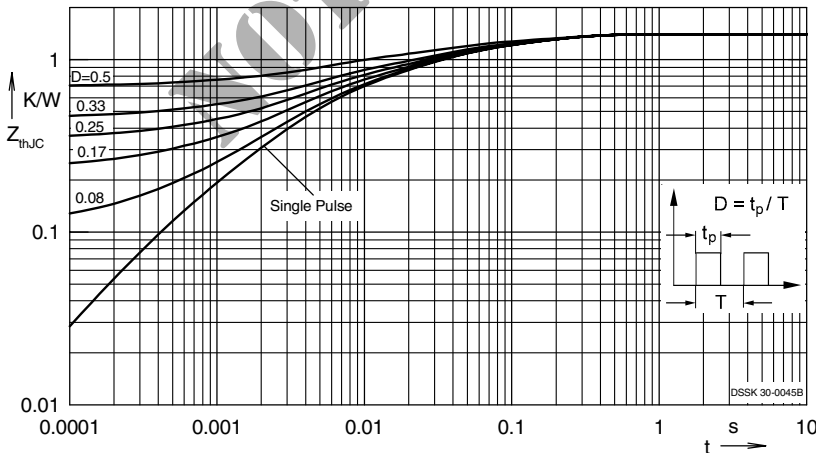


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode

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